

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

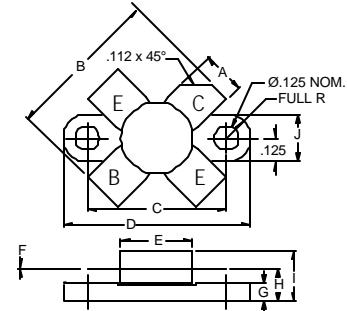
The ASI HF75-50F is Designed for

**FEATURES:**

- $P_G = 14$  dB min. at 75 W/30 MHz
- $IMD_3 = 50$  dBc max. at 75 W(PEP)
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	3.25 A
$V_{CB0}$	110 V
$V_{CEO}$	55 V
$V_{EBO}$	4.0 V
$P_{DISS}$	127 W @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+200^\circ C$
$T_{STG}$	$-65^\circ C$ to $+150^\circ C$
$q_{JC}$	2.0 $^\circ C/W$

**PACKAGE STYLE .380 4L FLG**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

**ORDER CODE: ASI10610**
**CHARACTERISTICS**  $T_C = 25^\circ C$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CES}$	$I_C = 100$ mA	110			V
$BV_{CEO}$	$I_C = 200$ mA	55			V
$BV_{EBO}$	$I_E = 10$ mA	4.0			V
$h_{FE}$	$V_{CE} = 6.0$ V $I_C = 1.4$ A	19	---	50	---
$C_{ob}$	$V_{CB} = 50$ V $f = 1.0$ MHz			100	pF
$G_P$		14	---		dB
$IMD_3$	$V_{CE} = 50$ V $P_{OUT} = 75$ W(PEP)	---	---	-30	dBc
$h_c$		37			%